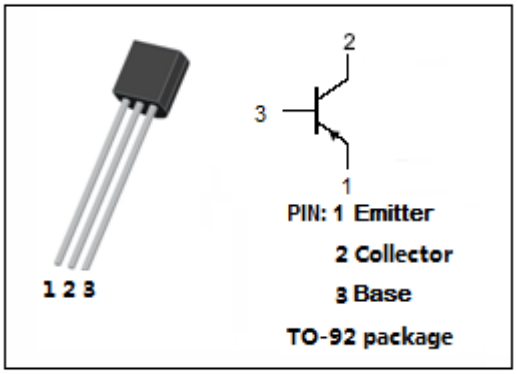
# *isc* Silicon PNP Transistor 2SA1082




## DESCRIPTION

• High Voltage

## APPLICATIONS

• Design For Amplifier and general purpose applications

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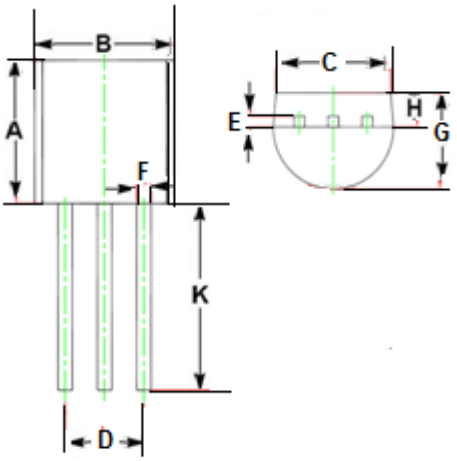
## ABSOLUTE MAXIMUM RATINGS($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | -120 | V |
| $V_{CEO}$ | Collector-Emitter Voltage | -120 | V |
| $V_{EBO}$ | Emitter-Base Voltage | -5 | V |
| $I_C$ | Collector Current-Continuous | -100 | mA |
| $P_D$ | Collector Power Dissipation@$T_A$=25℃ | 400 | mW |
| $T_J$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature Range | -55~150 | ℃ |




| DIM | mm MIN | MAX |
|---|---|---|
| A | 4.30 | 4.70 |
| B | 4.30 | 4.70 |
| C | 3.43 | |
| D | 2.44 | 2.64 |
| E | 0.36 | 0.51 |
| F | 0.38 | 0.55 |
| G | 3.30 | 3.70 |
| H | 1.10 | 1.40 |
| K | 14.10 | 14.50 |

## THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---|---|---|---|
| $R_{th\ j\text{-}a}$ | Thermal Resistance,Junction to Ambient | 312 | ℃/W |

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## ELECTRICAL CHARACTERISTICS

**$T_C$=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)CES}$ | Collector-Emitter Breakdown Voltage | $I_C$= -10μ A; $I_E$= 0 | -120 | | | V |
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C$= -1mA; $I_B$= 0 | -120 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E$= -10μ A; $I_C$= 0 | -5 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$=-10mA ; $I_B$= -1mA | | | -0.2 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C$= -2mA ; $V_{CE}$= -12V | | -0.6 | | V |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= -50V; $I_E$= 0 | | | -0.1 | μ A |
| $I_{EBO}$ | Emitter Cutoff Current | $V_{EB}$= -2V; $I_C$= 0 | | | -0.1 | μ A |
| $h_{FE}$ | DC Current Gain | $I_C$=-2mA ; $V_{CE}$= -12V | 250 | | 800 | |
| $f_T$ | Current-Gain—Bandwidth Product | $I_C$= -2mA; $V_{CE}$= -12V; f= 1MHz | | 90 | | MHz |
| Cob | Output Capacitance | $V_{CB}$ = −10 V, $I_E$ = 0, f =1.0MHz | | 3.5 | | pF |

◆ **$h_{FE}$ Classifications**

| D | E |
|---|---|
| 250-500 | 400-800 |